

Fabrication of Photo-carrier Transfer Channel for Near Infrared Up-conversion Coupled Photocathode Via Sandwiched-like Nanostructure

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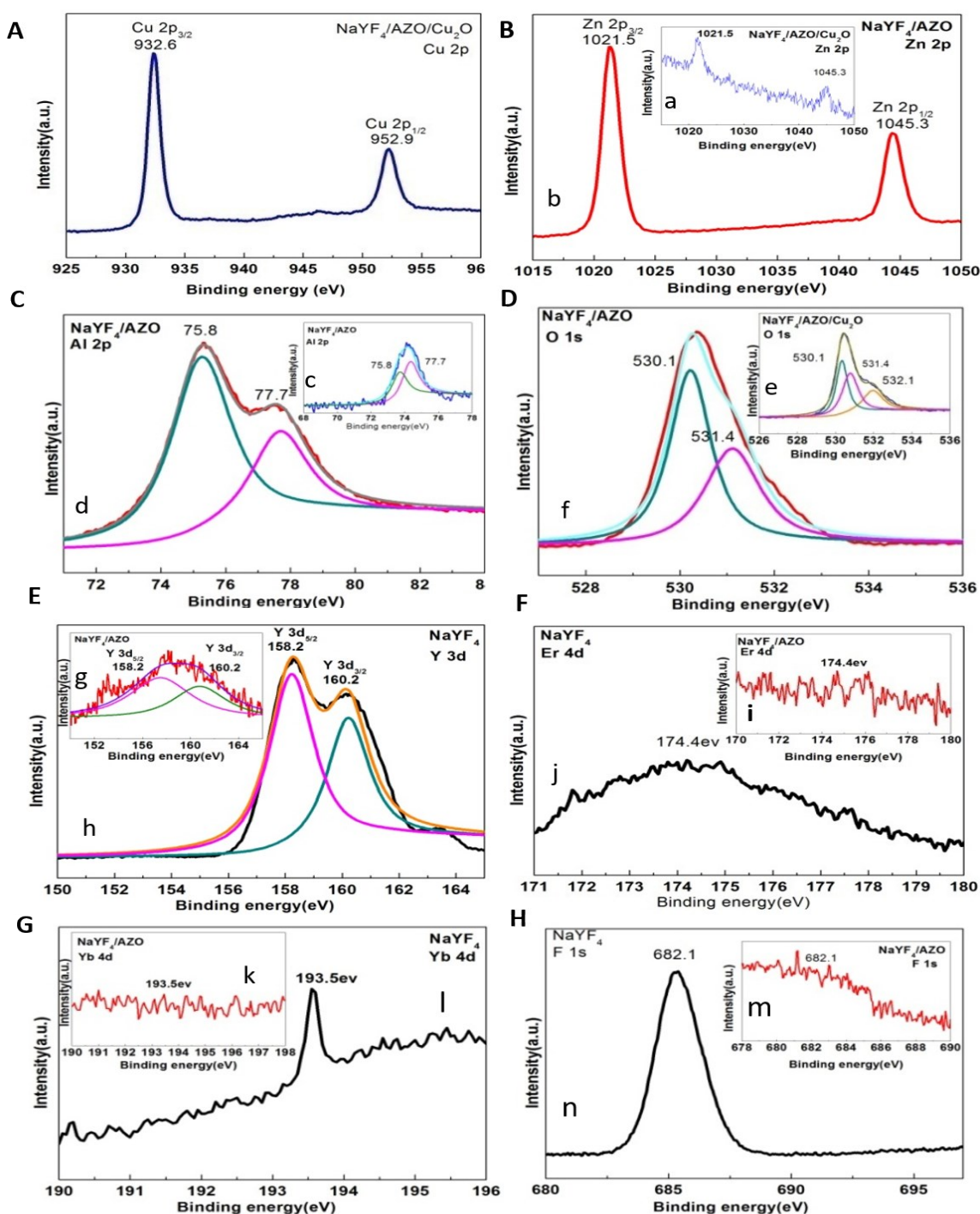


Figure S1. XPS spectra depicting peaks due to A) Cu 2p, B) Zn 2p, C) Al 2p, D) O 1s, E) Y 3d, F) Er 4d, G) Yb 4d, H) F 1s in NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O sandwiched-like composite thin film.

Fig.S1 shows the X-ray photoelectron spectroscopy (XPS) survey spectra of Cu, Zn, Al, O elements in NaYF₄:Er³⁺-Yb³⁺, NaYF₄:Er³⁺-Yb³⁺/AZO, and NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O composite films. **Fig. S1A** is the XPS spectra of Cu 2*p* in NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O sandwiched-like composite thin film, the Cu 2*p*_{3/2} and Cu 2*p*_{1/2} can be observed at 932.6 eV and 952.9 eV, respectively. In **Curve S1a**, the NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O sandwiched-like composite thin film shows the presence of Zn 2*p* at 1021.5 eV and 1045.3 eV, and the peaks of Zn 2*p* in NaYF₄:Er³⁺-Yb³⁺/AZO composite thin film are shown in **Curve S1b**, the **Fig.S1B** indicates the Zn 2*p* comes from AZO only. As shown in **Curve S1c** and **Curve S1d**, Al 2*p* can be observed at 75.8 eV and 77.7 eV, **Fig. S1C** indicates that Al 2*p* comes from AZO only. Due to Cu-O bonds, Zn-O bonds and Al-O bonds, in **CurveS1e** the presence of O 1*s* is observed on NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O at 530.1 eV, 531.4 eV and 532.1 eV, respectively, and in **CurveS1f**, O1*s* peaks can be observed on NaYF₄:Er³⁺-Yb³⁺/AZO at 530.1 eV, 531.4 eV, attribute to Zn-O bonds and Al-O bonds. The **Fig. S1D** indicates that there are only ZnO, Cu₂O and Al₂O₃ exist in NaYF₄:Er³⁺-Yb³⁺/AZO, and NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O composite films. In NaYF₄:Er³⁺-Yb³⁺ thin film, the peaks at 158.2 eV and 160.2 eV contributed by Y3*d*_{5/2} and Y3*d*_{3/2} can be seen in **Curve S1g**, in NaYF₄:Er³⁺-Yb³⁺/AZO composite film, the peaks are in same location shown by **Curve S1h**, the **Fig. S1E** certify the existence of NaYF₄. As shown in **Curve S1i**, the peak of Er4*d* in NaYF₄:Er³⁺-Yb³⁺/AZO composite film is obscured, in NaYF₄:Er³⁺-Yb³⁺ thin film, the peaks at 174.4 eV contributed by Er4*d* can be seen in **Curve S1j**, the **Fig.S1F** certify that the Er element has been doped in NaYF₄ successfully. In **Curve S1k** the peak of Yb4*d* in NaYF₄:Er³⁺-Yb³⁺/AZO composite film is obscured, in NaYF₄:Er³⁺-Yb³⁺ thin film, the peaks at 174.4 eV contributed by Er4*d* can be seen in **Curve S1j**, the **Fig S1G** certify that the Yb element has been doped in NaYF₄ successfully. The **Fig. S1H** indicates the existence of F.

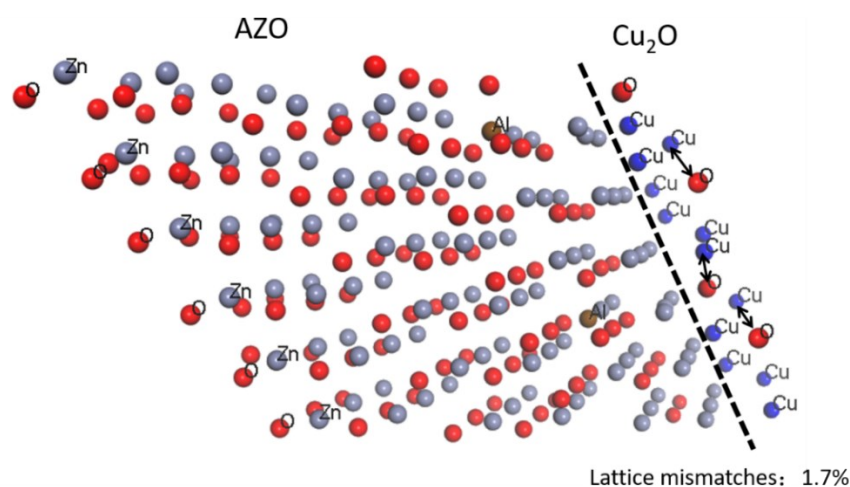


Figure S2. The lattice mismatch between AZO and Cu₂O.

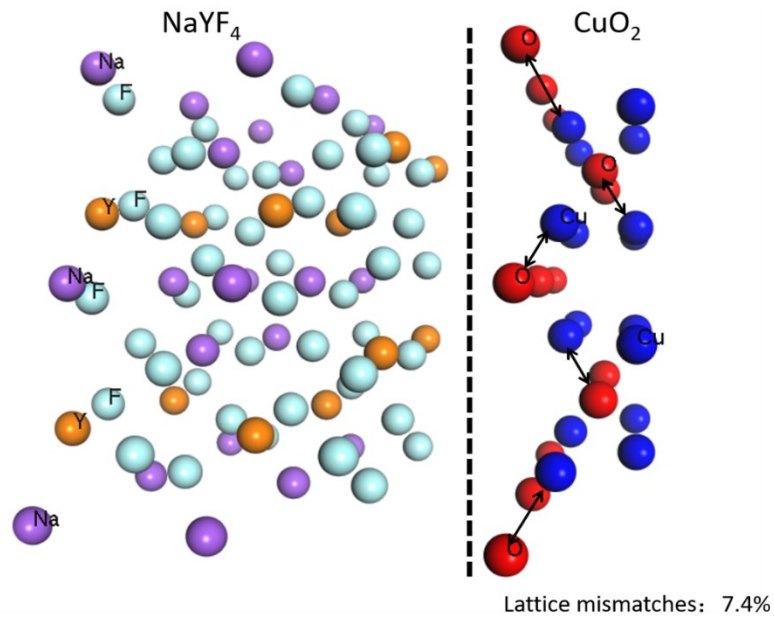


Figure S3. The lattice mismatch between NaYF₄ and Cu₂O.

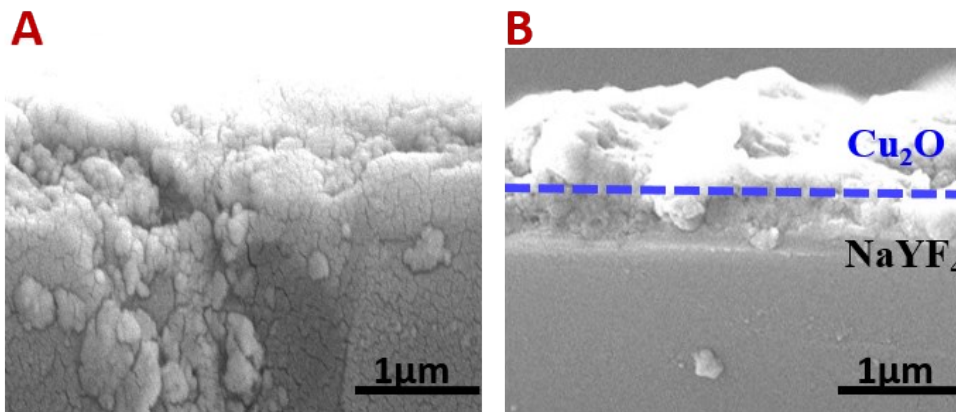


Fig. S4. A) Cross-section SEM image of NaYF₄:Er³⁺-Yb³⁺ thin film. B) Cross-section SEM mapping of NaYF₄:Er³⁺-Yb³⁺/Cu₂O composite thin film.

Fig.S4 shows the cross-section SEM image of NaYF₄:Er³⁺-Yb³⁺ film and NaYF₄:Er³⁺-Yb³⁺/Cu₂O composite thin film, respectively. The Cu₂O above the NaYF₄:Er³⁺-Yb³⁺ has been deformation.

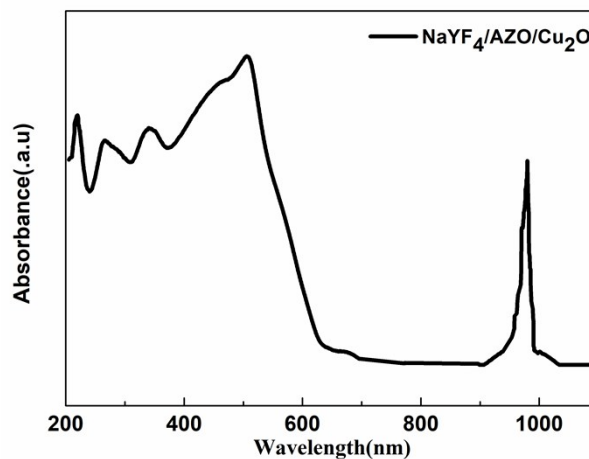


Figure S5. The UV-Vis of the NaYF₄/AZO/Cu₂O composite film.

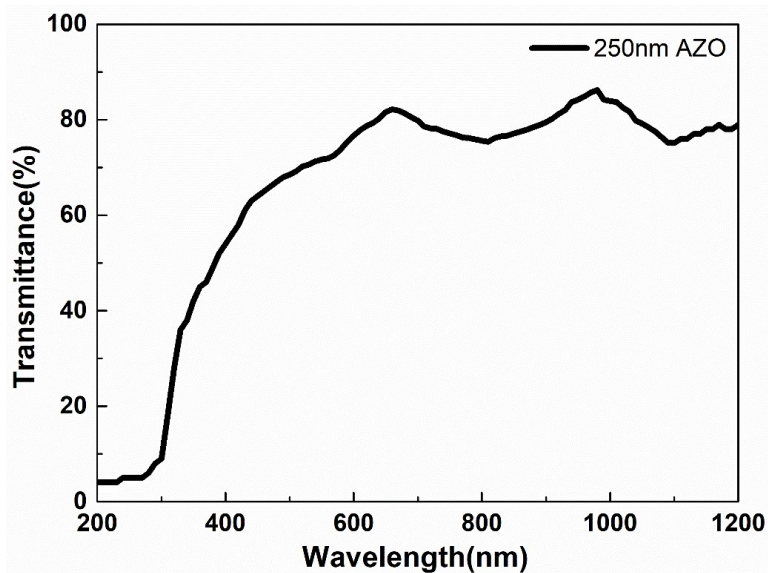


Figure S6. Transmission spectra of the 250 nm AZO film.

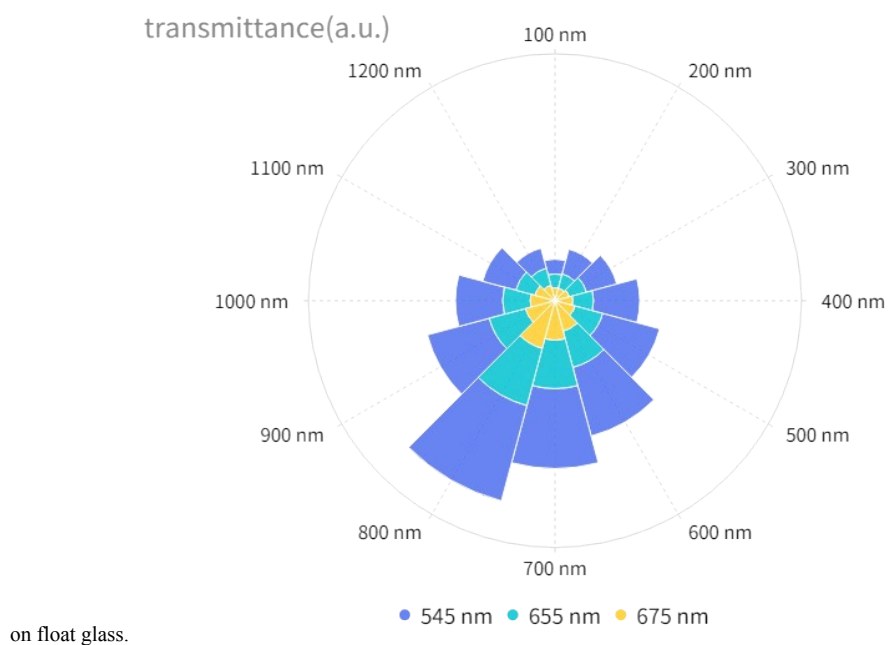


Figure S7. The UC fluorescence intensity of NaYF₄:Er³⁺-Yb³⁺ thin films with different thickness.

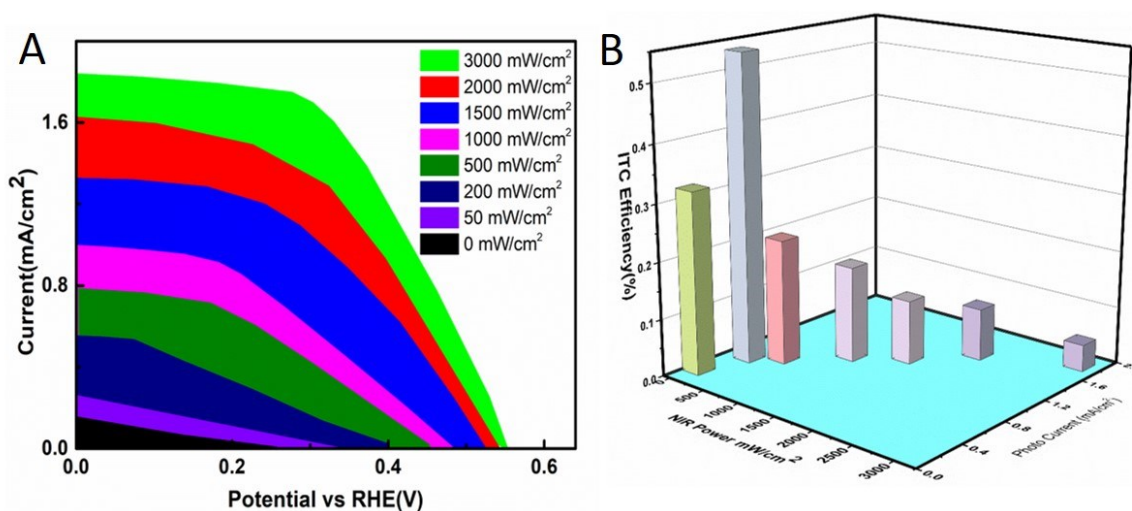


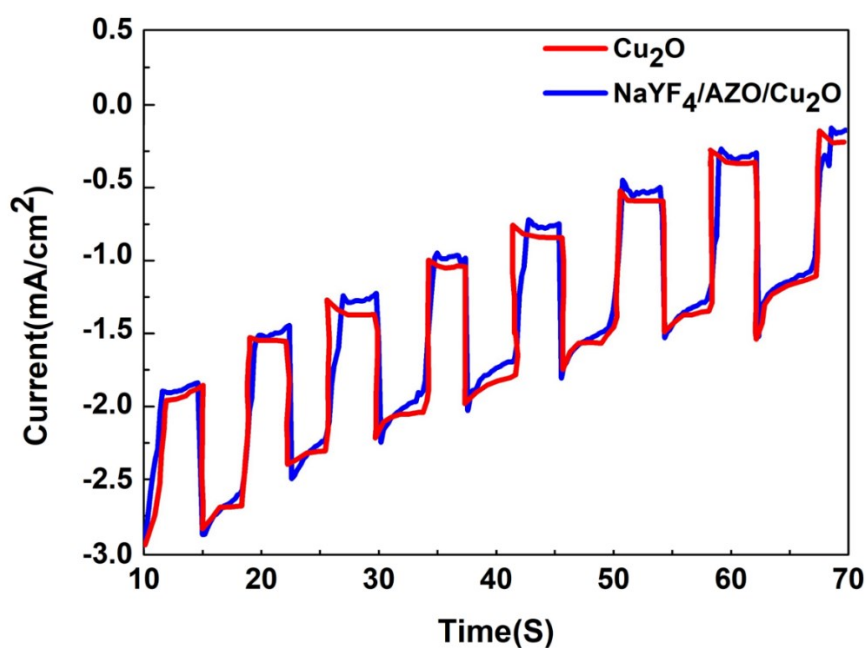
Fig. S8. A) I-V curves of NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O composite film were measured in 0.1M Na₂SO₄ (pH=6.1). B) ITC

of NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O composite film.

Fig.S8A is the photo-induced I-V curve of NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O photocathode by continuous 980 nm NIR excitation with different power density (0W excitation power means light off). **Fig.S8B** is the ITC efficiency of the NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O photocathode with different NIR power density. The ITC depend on photoelectric conversion efficiency, the maximum ITC efficiency of the NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O photocathode is 0.56% with 200 mW/cm² NIR excitation power. The Nernst **equation (1)** can convert potential vs. Ag/AgCl into the RHE potential. The ITC was calculated from the I-V curve with **equation (2)** in **Fig.S8B**, the I means the photocurrent, V is the bias voltage, and P_{light} means the NIR excitation power.

$$E_{RHE} = E_{Ag/AgCl} + 0.059 pH \quad (1)$$

$$ITC(\%) = \frac{\int_{V_{RHE}} IdV - \int_{V_{RHE}} I_{dark} dV}{P_{light}} \quad (2)$$



FigureS9. I-T curves of NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O photocathode and Cu₂O photocathode by sunlight from a Xe lamp.

Fig. S9 is the photo-induced I-T curves of NaYF₄:Er³⁺-Yb³⁺/AZO/Cu₂O and Cu₂O photocathodes at bias potential 0.5 V by sunlight on/off. The Cu₂O is not stable in sunlight, it caused the dark photocurrent has been increased. The percentage of 980 nm photon is very low in solar spectrum, so the PEC performance only can be limitedly improved.

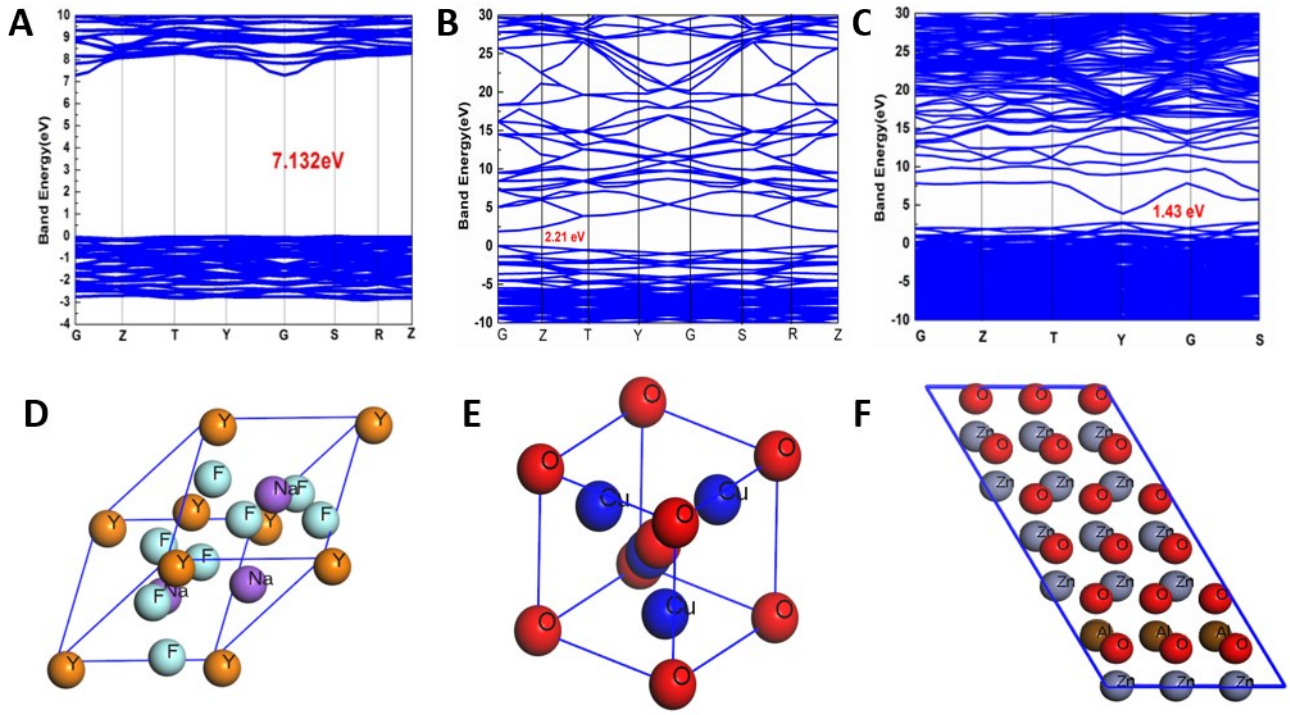


Fig. S10. A-C) The DOS of NaYF₄, Cu₂O and AZO. D-F) The crystal structure of NaYF₄ and Cu₂O, AZO.

The Density of State (DOS) of NaYF₄:Er³⁺-Yb³⁺, AZO and Cu₂O and corresponding crystal structure has been showed in **Fig S10**. According to **equation (3)**, the electron effective mass has been calculated, the E is the bottom of conduct band.

$$m_{e^*} = \hbar^2 \left(\frac{d^2 E}{d^2 \kappa} \right)^{-1} \quad (3)$$